74LVC1G53-Q100

2-channel analog multiplexer/demultiplexer

Rev. 1 — 29 January 2013 Product data sheet

1. General description

The 74LVC1G53-Q100 is a low-power, low-voltage, high-speed, Si-gate CMOS device.

The 74LVC1G53-Q100 provides one analog multiplexer/demultiplexer with a digital select input (S), two independent inputs/outputs (Y0 and Y1), a common input/output (Z) and an active LOW enable input ($\overline{E}$). When pin $\overline{E}$ is HIGH, the switch is turned off.

Schmitt-trigger action at the select and enable inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 1.65 V to 5.5 V.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from −40 °C to +85 °C and from −40 °C to +125 °C
- Wide supply voltage range from 1.65 V to 5.5 V
- Very low ON resistance:
  - 7.5 Ω (typical) at V_{CC} = 2.7 V
  - 6.5 Ω (typical) at V_{CC} = 3.3 V
  - 6 Ω (typical) at V_{CC} = 5 V
- Switch current capability of 32 mA
- High noise immunity
- CMOS low power consumption
- TTL interface compatibility at 3.3 V
- Latch-up performance meets requirements of JESD 78 Class I
- Multiple package options
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC1G53DP-Q100	−40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74LVC1G53DC-Q100	−40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1

4. Marking

Table 2. Marking codes

Type number	Marking code[1]
74LVC1G53DC-Q100	V53
74LVC1G53DP-Q100	V53

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

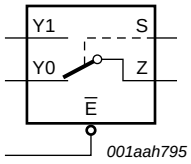


Fig 1. Logic symbol

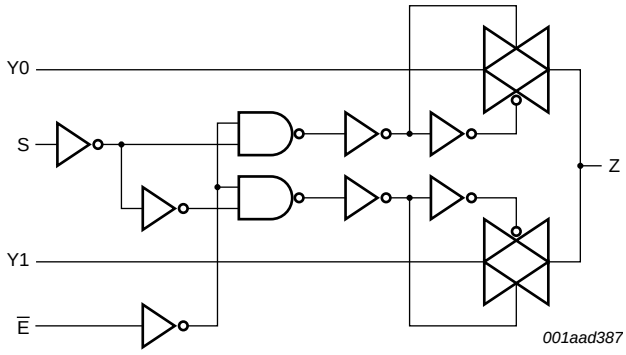


Fig 2. Logic diagram

6. Pinning information

6.1 Pinning

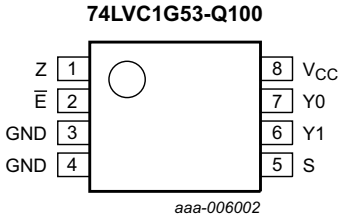


Fig 3. Pin configuration SOT505-2 and SOT765-1

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
Z	1	common output or input
$\overline{E}$	2	enable input (active LOW)
GND	3	ground (0 V)
GND	4	ground (0 V)
S	5	select input
Y1	6	independent input or output
Y0	7	independent input or output
V_{CC}	8	supply voltage

7. Functional description

Table 4. Function table[1]

Input		Channel on
S	$\overline{E}$	
L	L	Y0 to Z or Z to Y0
H	L	Y1 to Z or Z to Y1
X	H	Z (switch off)

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			−0.5	+6.5	V
V_I	input voltage		[1]	−0.5	+6.5	V
I_{IK}	input clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V		−50	-	mA
I_{SK}	switch clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V		-	±50	mA
V_{SW}	switch voltage	enable and disable mode	[2]	−0.5	$V_{CC} + 0.5$	V
I_{SW}	switch current	$V_{SW} > -0.5$ V or $V_{SW} < V_{CC} + 0.5$ V		-	±50	mA
I_{CC}	supply current			-	100	mA
I_{GND}	ground current			−100	-	mA
T_{stg}	storage temperature			−65	+150	°C
P_{tot}	total power dissipation	T_{amb} = −40 °C to +125 °C	[3]	-	250	mW

[1] The minimum input voltage rating may be exceeded if the input current rating is observed.

[2] The minimum and maximum switch voltage ratings may be exceeded if the switch clamping current rating is observed.

[3] For TSSOP8 packages: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.
For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly with 8.0 mW/K.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			1.65	5.5	V
V_I	input voltage			0	5.5	V
V_{SW}	switch voltage	enable and disable mode	[1]	0	V_{CC}	V
T_{amb}	ambient temperature			−40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 1.65 V to 2.7 V	[2]	-	20	ns/V
		V_{CC} = 2.7 V to 5.5 V	[2]	-	10	ns/V

[1] To avoid sinking GND current from terminal Z when switch current flows in terminal Yn, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal Z, no GND current flows from terminal Yn. In this case, there is no limit for the voltage drop across the switch.

[2] Applies to control signal levels.

10. Static characteristics

Table 7. Static characteristics

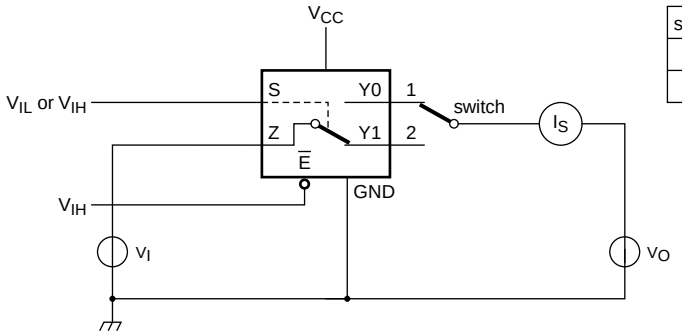
At recommended operating conditions; voltages are referenced to GND (ground 0 V).

Symbol	Parameter	Conditions		T_{amb} = –40 °C to +85 °C			T_{amb} = –40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	
V_{IH}	HIGH-level input voltage	V_{CC} = 1.65 V to 1.95 V		0.65 × V_{CC}	-	-	0.65 × V_{CC}	-	V
		V_{CC} = 2.3 V to 2.7 V		1.7	-	-	1.7	-	V
		V_{CC} = 3 V to 3.6 V		2.0	-	-	2.0	-	V
		V_{CC} = 4.5 V to 5.5 V		0.7 × V_{CC}	-	-	0.7 × V_{CC}	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 1.65 V to 1.95 V		-	-	0.35 × V_{CC}	-	0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V		-	-	0.7	-	0.7	V
		V_{CC} = 3 V to 3.6 V		-	-	0.8	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V		-	-	0.3 × V_{CC}	-	0.3 × V_{CC}	V
I_I	input leakage current	pin S and pin $\overline{E}$; V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	[2]	-	±0.1	±2	-	±10	μA
$I_{S(OFF)}$	OFF-state leakage current	V_{CC} = 5.5 V; see Figure 4	[2]	-	±0.1	±5	-	±20	μA
$I_{S(ON)}$	ON-state leakage current	V_{CC} = 5.5 V; see Figure 5	[2]	-	±0.1	±5	-	±20	μA
I_{CC}	supply current	V_I = 5.5 V or GND; V_{SW} = GND or V_{CC}; V_{CC} = 1.65 V to 5.5 V	[2]	-	0.1	10	-	40	μA
ΔI_{CC}	additional supply current	pin S and pin $\overline{E}$; V_I = V_{CC} − 0.6 V; V_{SW} = GND or V_{CC}; V_{CC} = 5.5 V	[2]	-	5	500	-	5000	μA
C_I	input capacitance			-	2.5	-	-	-	pF
$C_{S(OFF)}$	OFF-state capacitance			-	6.0	-	-	-	pF
$C_{S(ON)}$	ON-state capacitance			-	18	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C.

[2] These typical values are measured at V_{CC} = 3.3 V.

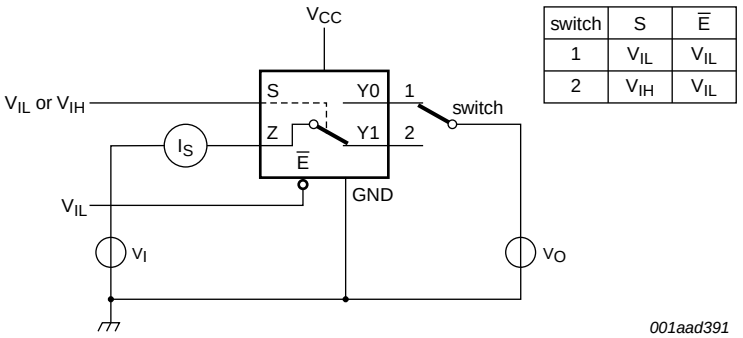
10.1 Test circuits



switch	S	$\overline{E}$
1	V_{IL}	V_{IH}
2	V_{IH}	V_{IH}

$V_I = V_{CC}$ or GND; V_O = GND or V_{CC}.

Fig 4. Test circuit for measuring OFF-state leakage current



switch	S	$\overline{E}$
1	V_{IL}	V_{IL}
2	V_{IH}	V_{IL}

$V_I = V_{CC}$ or GND and V_O = open circuit.

Fig 5. Test circuit for measuring ON-state leakage current

10.2 ON resistance

Table 8. ON resistance

At recommended operating conditions; voltages are referenced to GND (ground 0 V); for graphs see Figure 7 to Figure 12.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
$R_{ON(peak)}$	ON resistance (peak)	V_I = GND to V_{CC}; see Figure 6						
		I_{SW} = 4 mA; V_{CC} = 1.65 V to 1.95 V	-	34.0	130	-	195	Ω
		I_{SW} = 8 mA; V_{CC} = 2.3 V to 2.7 V	-	12.0	30	-	45	Ω
		I_{SW} = 12 mA; V_{CC} = 2.7 V	-	10.4	25	-	38	Ω
		I_{SW} = 24 mA; V_{CC} = 3 V to 3.6 V	-	7.8	20	-	30	Ω
		I_{SW} = 32 mA; V_{CC} = 4.5 V to 5.5 V	-	6.2	15	-	23	Ω

Table 8. ON resistance *...continued*

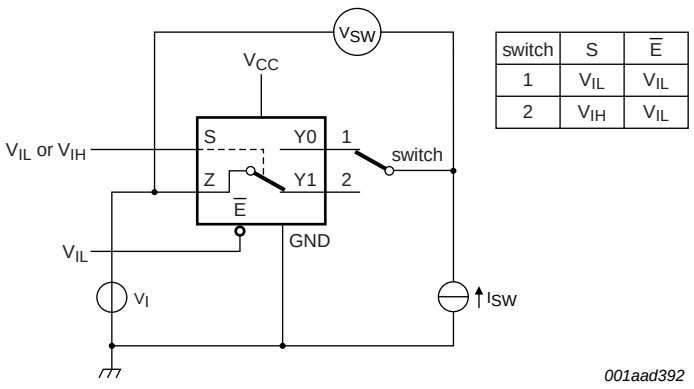
At recommended operating conditions; voltages are referenced to GND (ground 0 V); for graphs see Figure 7 to Figure 12.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
$R_{ON(rail)}$	ON resistance (rail)	V_I = GND; see Figure 6						
		I_{SW} = 4 mA; V_{CC} = 1.65 V to 1.95 V	-	8.2	18	-	27	Ω
		I_{SW} = 8 mA; V_{CC} = 2.3 V to 2.7 V	-	7.1	16	-	24	Ω
		I_{SW} = 12 mA; V_{CC} = 2.7 V	-	6.9	14	-	21	Ω
		I_{SW} = 24 mA; V_{CC} = 3 V to 3.6 V	-	6.5	12	-	18	Ω
		I_{SW} = 32 mA; V_{CC} = 4.5 V to 5.5 V	-	5.8	10	-	15	Ω
		V_I = V_{CC}; see Figure 6						
		I_{SW} = 4 mA; V_{CC} = 1.65 V to 1.95 V	-	10.4	30	-	45	Ω
		I_{SW} = 8 mA; V_{CC} = 2.3 V to 2.7 V	-	7.6	20	-	30	Ω
		I_{SW} = 12 mA; V_{CC} = 2.7 V	-	7.0	18	-	27	Ω
		I_{SW} = 24 mA; V_{CC} = 3 V to 3.6 V	-	6.1	15	-	23	Ω
		I_{SW} = 32 mA; V_{CC} = 4.5 V to 5.5 V	-	4.9	10	-	15	Ω
$R_{ON(flat)}$	ON resistance (flatness)	V_I = GND to V_{CC} [2]						
		I_{SW} = 4 mA; V_{CC} = 1.65 V to 1.95 V	-	26.0	-	-	-	Ω
		I_{SW} = 8 mA; V_{CC} = 2.3 V to 2.7 V	-	5.0	-	-	-	Ω
		I_{SW} = 12 mA; V_{CC} = 2.7 V	-	3.5	-	-	-	Ω
		I_{SW} = 24 mA; V_{CC} = 3 V to 3.6 V	-	2.0	-	-	-	Ω
		I_{SW} = 32 mA; V_{CC} = 4.5 V to 5.5 V	-	1.5	-	-	-	Ω

[1] Typical values are measured at T_{amb} = 25 °C and nominal V_{CC}.

[2] Flatness is defined as the difference between the maximum and minimum value of ON resistance measured at identical V_{CC} and temperature.

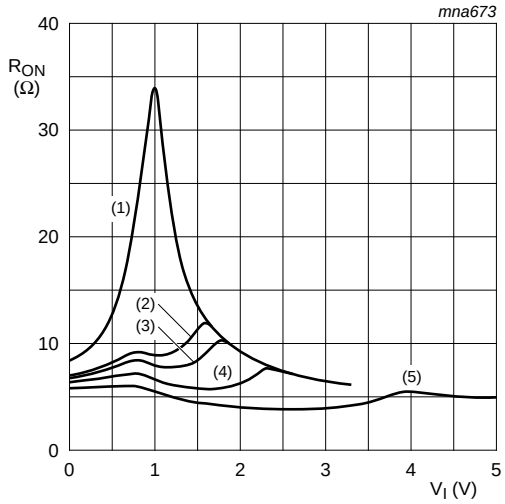
10.3 ON resistance test circuit and graphs



switch	S	$\overline{E}$
1	V_{IL}	V_{IL}
2	V_{IH}	V_{IL}

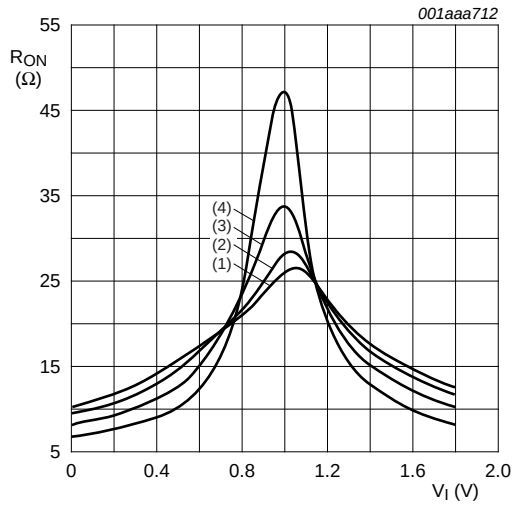
$R_{ON} = V_{SW} / I_{SW}$.

Fig 6. Test circuit for measuring ON resistance



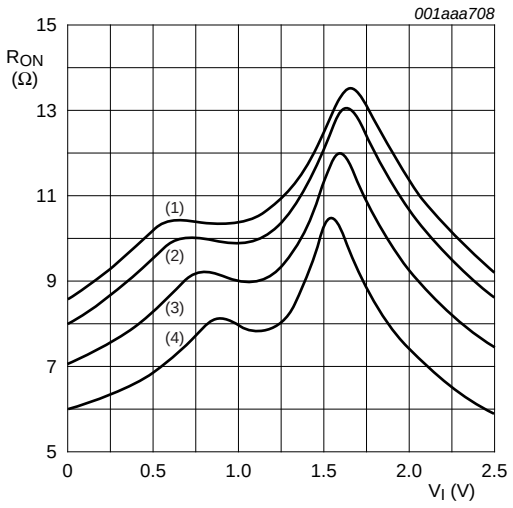
(1) V_{CC} = 1.8 V.
(2) V_{CC} = 2.5 V.
(3) V_{CC} = 2.7 V.
(4) V_{CC} = 3.3 V.
(5) V_{CC} = 5.0 V.

Fig 7. Typical ON resistance as a function of input voltage; T_{amb} = 25 °C



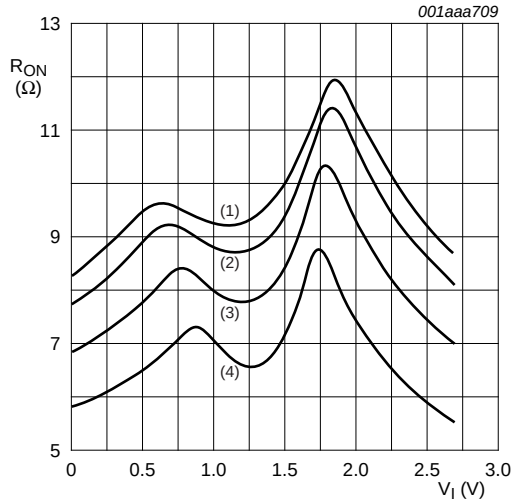
(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.
(4) T_{amb} = −40 °C.

Fig 8. ON resistance as a function of input voltage; V_{CC} = 1.8 V



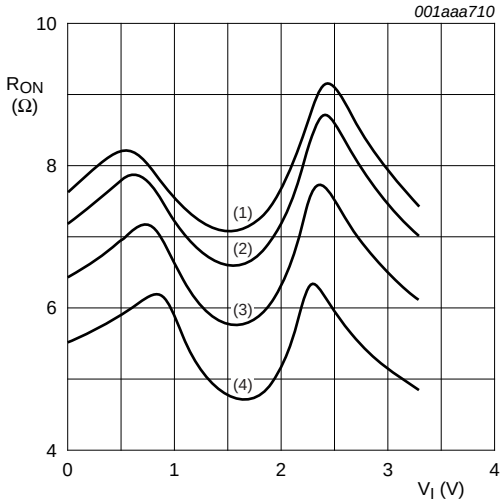
(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.
(4) T_{amb} = −40 °C.

Fig 9. ON resistance as a function of input voltage; V_{CC} = 2.5 V



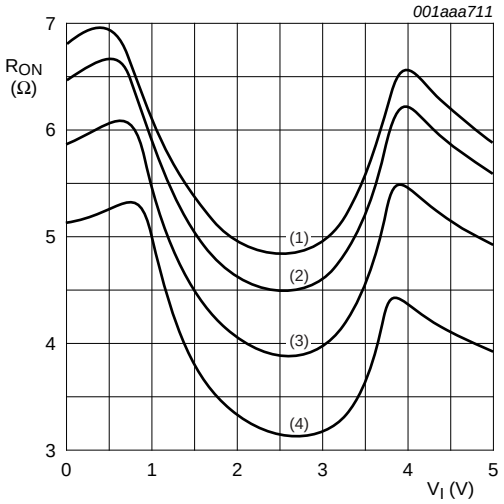
(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.
(4) T_{amb} = −40 °C.

Fig 10. ON resistance as a function of input voltage; V_{CC} = 2.7 V



(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.
(4) T_{amb} = −40 °C.

Fig 11. ON resistance as a function of input voltage; V_{CC} = 3.3 V



(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.
(4) T_{amb} = −40 °C.

Fig 12. ON resistance as a function of input voltage; V_{CC} = 5.0 V

11. Dynamic characteristics

Table 9. Dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for load circuit see Figure 15.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
t_{pd}	propagation delay	Z to Yn or Yn to Z; see Figure 13 [2][3]						
		V_{CC} = 1.65 V to 1.95 V	-	-	2	-	2.5	ns
		V_{CC} = 2.3 V to 2.7 V	-	-	1.2	-	1.5	ns
		V_{CC} = 2.7 V	-	-	1.0	-	1.25	ns
		V_{CC} = 3.0 V to 3.6 V	-	-	0.8	-	1.0	ns
		V_{CC} = 4.5 V to 5.5 V	-	-	0.6	-	0.8	ns
t_{en}	enable time	S to Z or Yn; see Figure 14 [4]						
		V_{CC} = 1.65 V to 1.95 V	2.6	6.7	10.3	2.6	12.9	ns
		V_{CC} = 2.3 V to 2.7 V	1.9	4.1	6.4	1.9	8.0	ns
		V_{CC} = 2.7 V	1.9	4.0	5.5	1.8	7.0	ns
		V_{CC} = 3.0 V to 3.6 V	1.8	3.4	5.0	1.8	6.3	ns
		V_{CC} = 4.5 V to 5.5 V	1.3	2.6	3.8	1.3	4.8	ns
		$\overline{E}$ to Z or Yn; see Figure 14 [4]						
		V_{CC} = 1.65 V to 1.95 V	1.9	4.0	7.3	1.9	9.2	ns
		V_{CC} = 2.3 V to 2.7 V	1.4	2.5	4.4	1.4	5.5	ns
		V_{CC} = 2.7 V	1.1	2.6	3.9	1.1	4.9	ns
		V_{CC} = 3.0 V to 3.6 V	1.2	2.2	3.8	1.2	4.8	ns
		V_{CC} = 4.5 V to 5.5 V	1.0	1.7	2.6	1.0	3.3	ns
t_{dis}	disable time	S to Z or Yn; see Figure 14 [5]						
		V_{CC} = 1.65 V to 1.95 V	2.1	6.8	10.0	2.1	12.5	ns
		V_{CC} = 2.3 V to 2.7 V	1.4	3.7	6.1	1.4	7.7	ns
		V_{CC} = 2.7 V	1.4	4.9	6.2	1.4	7.8	ns
		V_{CC} = 3.0 V to 3.6 V	1.1	4.0	5.4	1.1	6.8	ns
		V_{CC} = 4.5 V to 5.5 V	1.0	2.9	3.8	1.0	4.8	ns
		$\overline{E}$ to Z or Yn; see Figure 14 [5]						
		V_{CC} = 1.65 V to 1.95 V	2.3	5.6	8.6	2.3	11.0	ns
		V_{CC} = 2.3 V to 2.7 V	1.2	3.2	4.8	1.2	6.0	ns
		V_{CC} = 2.7 V	1.4	4.0	5.2	1.4	6.5	ns
		V_{CC} = 3.0 V to 3.6 V	2.0	3.7	5.0	2.0	6.3	ns
		V_{CC} = 4.5 V to 5.5 V	1.3	2.9	3.8	1.3	4.8	ns

[1] Typical values are measured at T_{amb} = 25 °C and nominal V_{CC}.

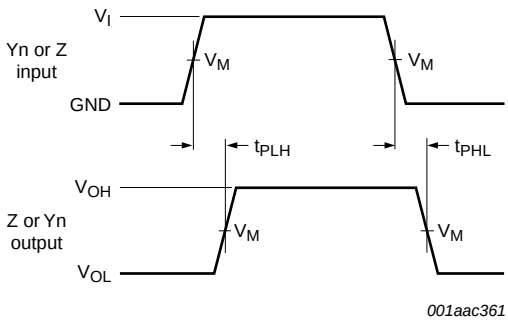
[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] Propagation delay is the calculated RC time constant of the typical ON resistance of the switch and the specified capacitance when driven by an ideal voltage source (zero output impedance).

[4] t_{en} is the same as t_{PZH} and t_{PZL}.

[5] t_{dis} is the same as t_{PLZ} and t_{PHZ}.

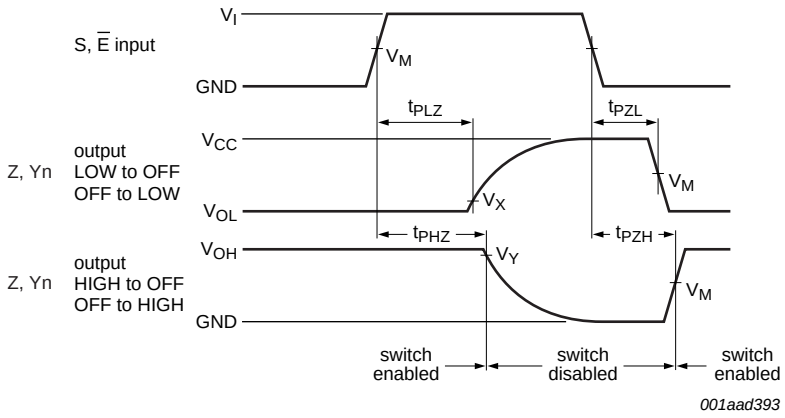
11.1 Waveforms and test circuits



Measurement points are given in Table 10.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 13. Input (Yn or Z) to output (Z or Yn) propagation delays



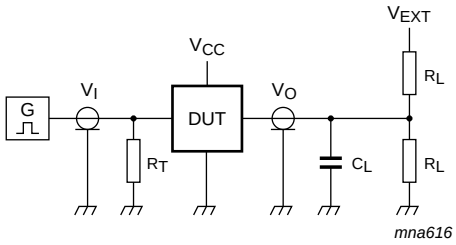
Measurement points are given in Table 10.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 14. Enable and disable times

Table 10. Measurement points

Supply voltage	Input	Output		
V_{CC}	V_M	V_M	V_X	V_Y
1.65 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V_{OL} + 0.15 V	V_{OH} − 0.15 V
2.7 V to 5.5 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V_{OL} + 0.3 V	V_{OH} − 0.3 V



Test data is given in Table 11.

Definitions test circuit:

R_T = Termination resistance (should be equal to output impedance Z_o of the pulse generator).

C_L = Load capacitance (including jig and probe capacitance).

R_L = Load resistance.

V_{EXT} = External voltage for measuring switching times.

Fig 15. Test circuit for measuring switching times

Table 11. Test data

Supply voltage	Input		Load		V_{EXT}		
V_{CC}	V_I	t_r, t_f	C_L	R_L	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
1.65 V to 1.95 V	V_{CC}	≤ 2.0 ns	30 pF	1 kΩ	open	GND	2 × V_{CC}
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	500 Ω	open	GND	2 × V_{CC}
2.7 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open	GND	2 × V_{CC}
3 V to 3.6 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open	GND	2 × V_{CC}
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open	GND	2 × V_{CC}

11.2 Additional dynamic characteristics

Table 12. Additional dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T_{amb} = 25 °C.

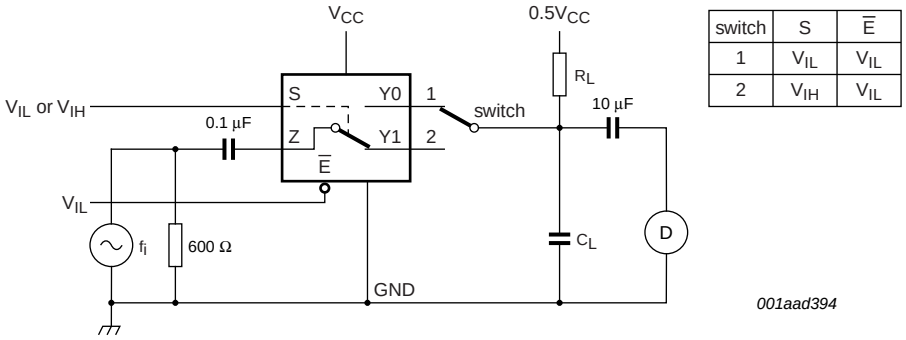
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
THD	total harmonic distortion	f_i = 600 Hz to 20 kHz; R_L = 600 Ω; C_L = 50 pF; V_I = 0.5 V (p-p); see Figure 16				
		V_{CC} = 1.65 V	-	0.260	-	%
		V_{CC} = 2.3 V	-	0.078	-	%
		V_{CC} = 3.0 V	-	0.078	-	%
		V_{CC} = 4.5 V	-	0.078	-	%
$f_{(-3dB)}$	−3 dB frequency response	R_L = 50 Ω; C_L = 5 pF; see Figure 17				
		V_{CC} = 1.65 V	-	200	-	MHz
		V_{CC} = 2.3 V	-	300	-	MHz
		V_{CC} = 3.0 V	-	300	-	MHz
		V_{CC} = 4.5 V	-	300	-	MHz

Table 12. Additional dynamic characteristics *...continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T_{amb} = 25 °C.

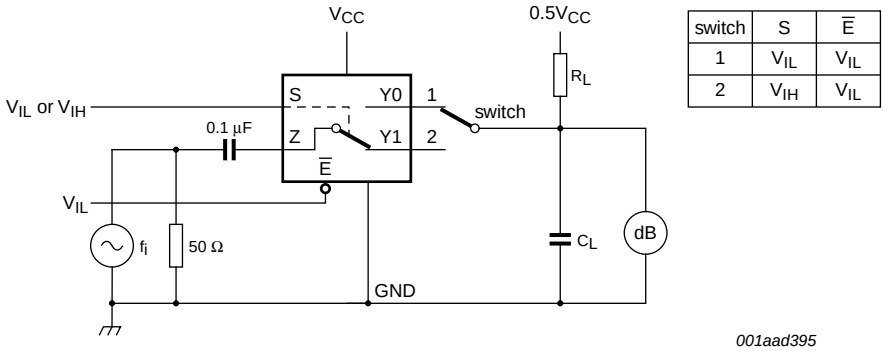
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
α_{iso}	isolation (OFF-state)	R_L = 50 Ω; C_L = 5 pF; f_i = 10 MHz; see Figure 18				
		V_{CC} = 1.65 V	-	−42	-	dB
		V_{CC} = 2.3 V	-	−42	-	dB
		V_{CC} = 3.0 V	-	−40	-	dB
		V_{CC} = 4.5 V	-	−40	-	dB
Q_{inj}	charge injection	C_L = 0.1 nF; V_{gen} = 0 V; R_{gen} = 0 Ω; f_i = 1 MHz; R_L = 1 MΩ; see Figure 19				
		V_{CC} = 1.8 V	-	3.3	-	pC
		V_{CC} = 2.5 V	-	4.1	-	pC
		V_{CC} = 3.3 V	-	5.0	-	pC
		V_{CC} = 4.5 V	-	6.4	-	pC
		V_{CC} = 5.5 V	-	7.5	-	pC

11.3 Test circuits



switch	S	$\overline{E}$
1	V_{IL}	V_{IL}
2	V_{IH}	V_{IL}

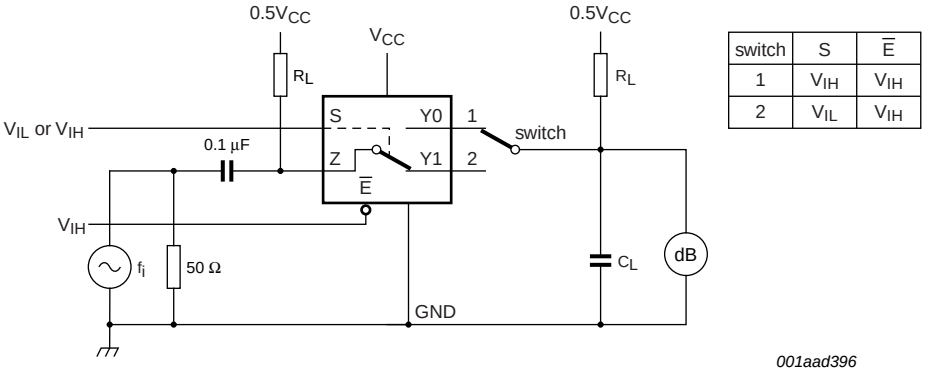
Fig 16. Test circuit for measuring total harmonic distortion



switch	S	$\overline{E}$
1	V_{IL}	V_{IL}
2	V_{IH}	V_{IL}

Adjust f_i voltage to obtain 0 dBm level at output. Increase f_i frequency until dB meter reads −3 dB.

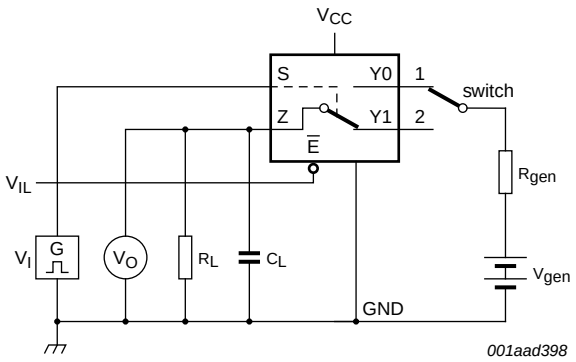
Fig 17. Test circuit for measuring the frequency response when switch is in ON-state



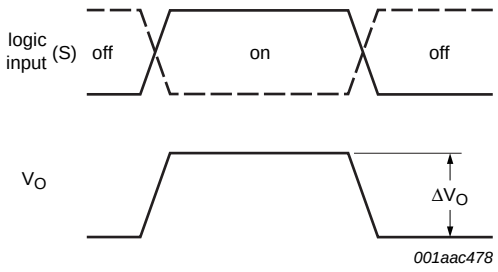
switch	S	$\overline{E}$
1	V_{IH}	V_{IH}
2	V_{IL}	V_{IH}

Adjust f_i voltage to obtain 0 dBm level at input.

Fig 18. Test circuit for measuring isolation (OFF-state)



a. Test circuit



b. Input and output pulse definitions

$Q_{inj} = \Delta V_O \times C_L$.

ΔV_O = output voltage variation.

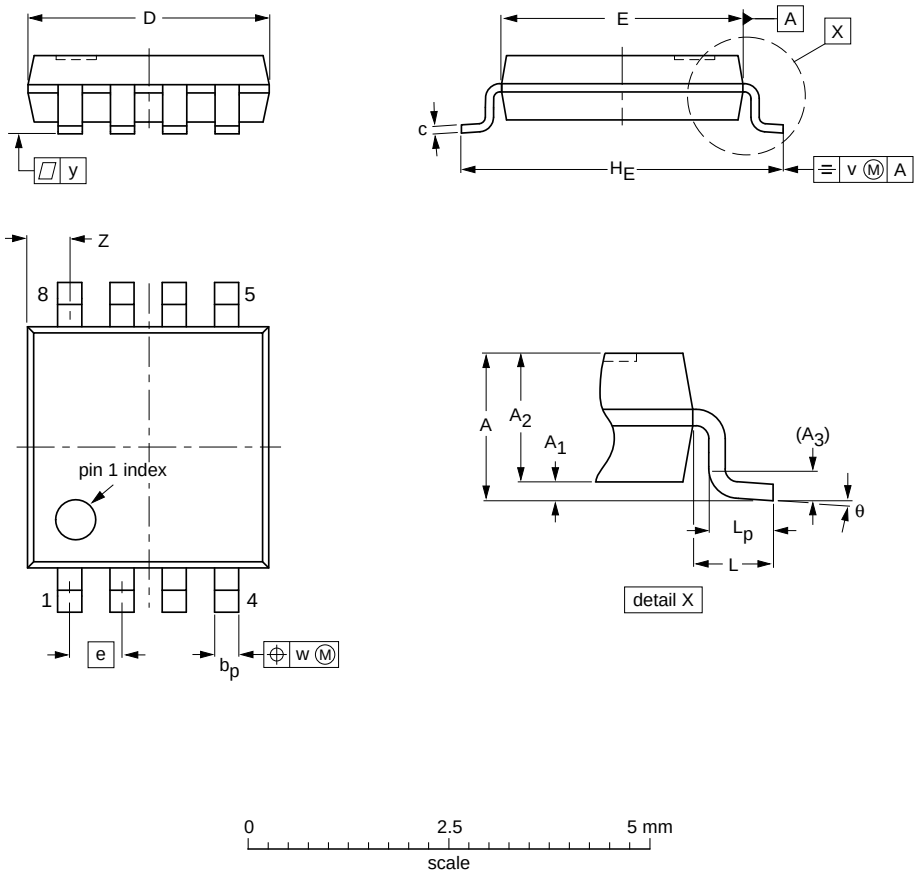
R_{gen} = generator resistance.

V_{gen} = generator voltage.

Fig 19. Test circuit for measuring charge injection

12. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	v	w	y	$Z^{(1)}$	θ
mm	1.1	0.15 0.00	0.95 0.75	0.25	0.38 0.22	0.18 0.08	3.1 2.9	3.1 2.9	0.65	4.1 3.9	0.5	0.47 0.33	0.2	0.13	0.1	0.70 0.35	8° 0°

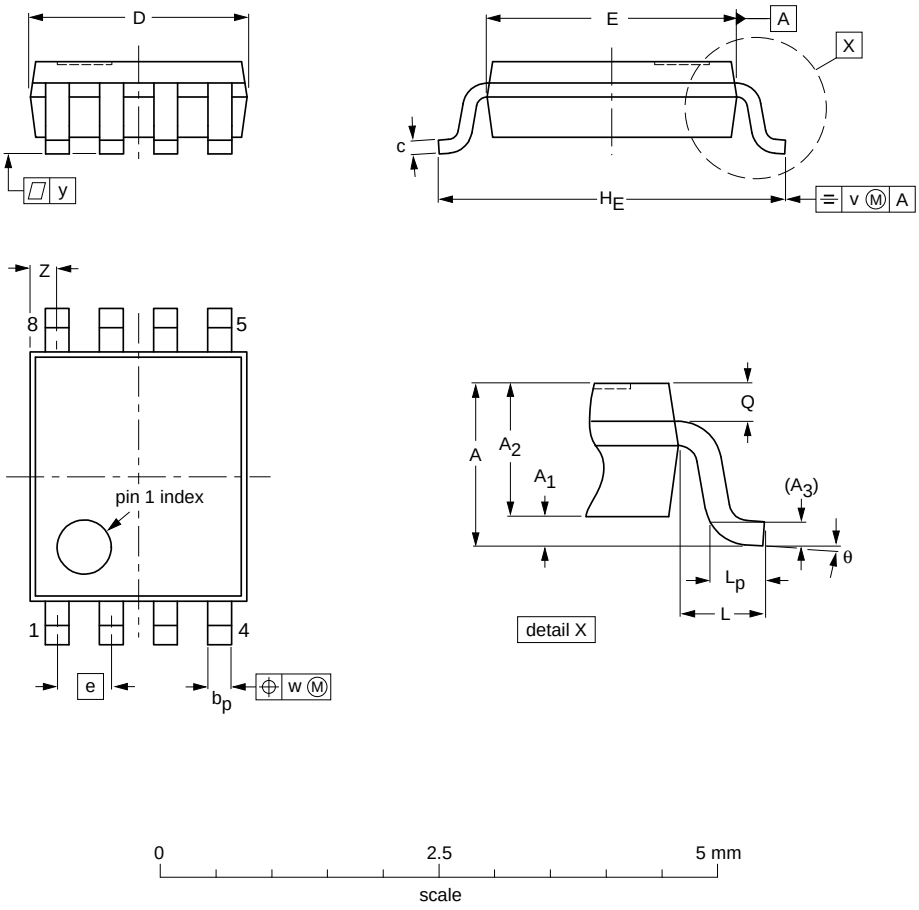
Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT505-2		- - -				02-01-16

Fig 20. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm **SOT765-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(2)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT765-1		MO-187				02-06-07

Fig 21. Package outline SOT765-1 (VSSOP8)

13. Abbreviations

Table 13. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
TTL	Transistor-Transistor Logic
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
CDM	Charged Device Model
DUT	Device Under Test
MIL	Military

14. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC1G53_Q100 v.1	20130129	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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17. Contents

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